

N-Channel Enhancement Mode Power MOSFET

Description

The GT048N10M uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} 100V
- I_D (at $V_{GS} = 10V$) 110A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 5.5m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 7m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-263

Ordering Information

Device	Package	Marking	Packaging
GT048N10M	TO-263	GT048N10	800pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current	I_D	110	A
		70	
Pulsed Drain Current (note1)	I_{DM}	440	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	150	W
Single pulse avalanche energy (note2)	E_{AS}	210	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	R_{thJC}	0.83	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 40A$	--	4.7	5.5	m Ω
		$V_{GS} = 4.5V, I_D = 40A$	--	5.7	7.0	
Forward Transconductance	g_{FS}	$V_{GS} = 5V, I_D = 20A$	--	45	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 0.8MHz$	--	3220	--	pF
Output Capacitance	C_{oss}		--	1225	--	
Reverse Transfer Capacitance	C_{rss}		--	9	--	
Total Gate Charge	Q_g	$V_{DD} = 50V,$ $I_D = 20A,$ $V_{GS} = 10V$	--	68	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	
Gate-Drain Charge	Q_{gd}		--	16	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V,$ $I_D = 20A,$ $R_G = 2.2\Omega$	--	13	--	ns
Turn-on Rise Time	t_r		--	27	--	
Turn-off Delay Time	$t_{d(off)}$		--	24	--	
Turn-off Fall Time	t_f		--	5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ C$	--	--	110	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ C, I_{SD} = 20A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Charge	Q_{rr}	$I_F = 20A, V_{GS} = 0V$ $di/dt=600A/us$	--	116	--	nC
Reverse Recovery Time	T_{rr}		--	25	--	ns

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition : $T_J = 25^\circ\text{C}$, $V_{DD} = 50V$, $V_{GS} = 10V$, $L = 0.5mH$, $R_G = 25\Omega$

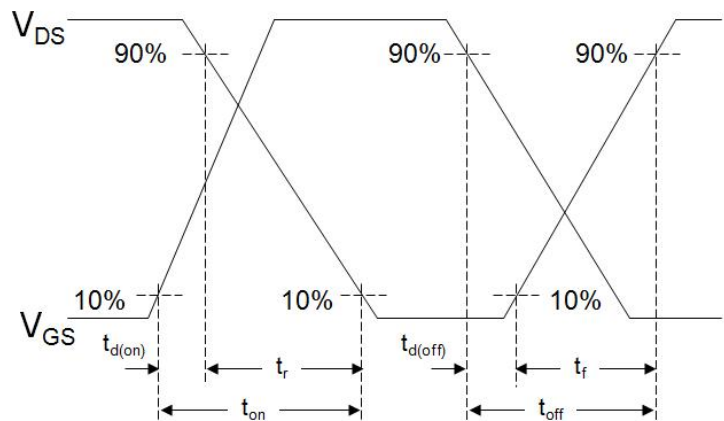
The table shows the minimum avalanche energy, which is 570mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

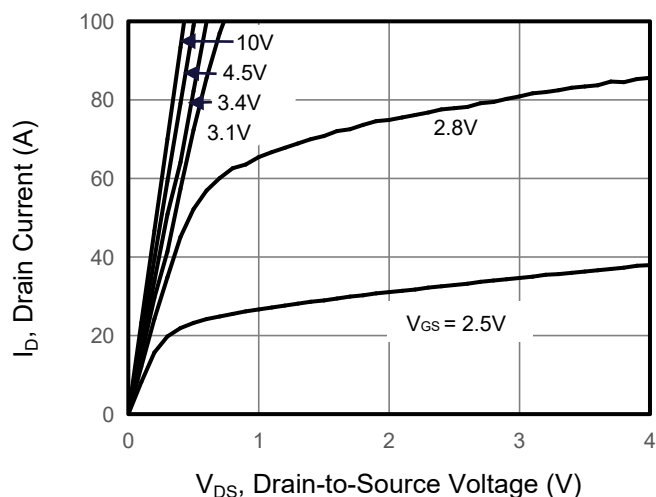


Figure 2. Transfer Characteristics

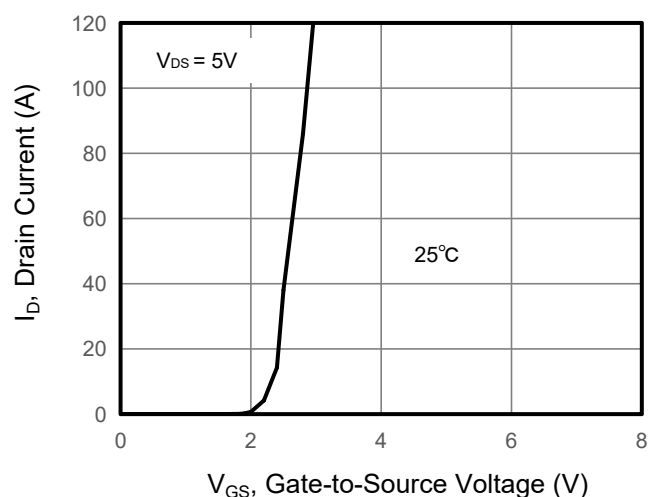


Figure 3. Drain Source On Resistance

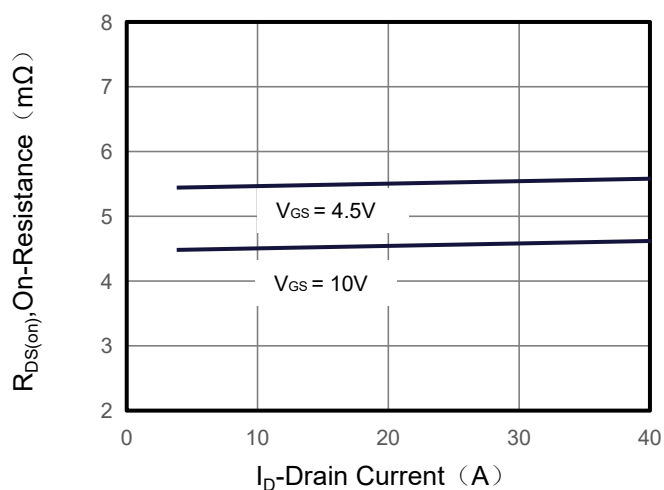


Figure 4. Gate Charge

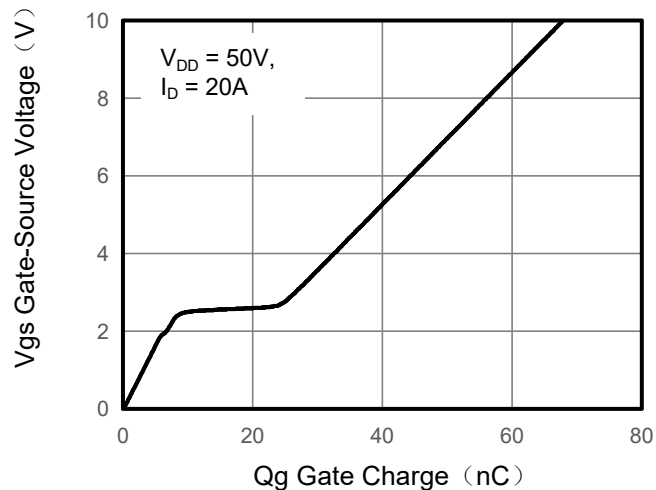


Figure 5. Capacitance

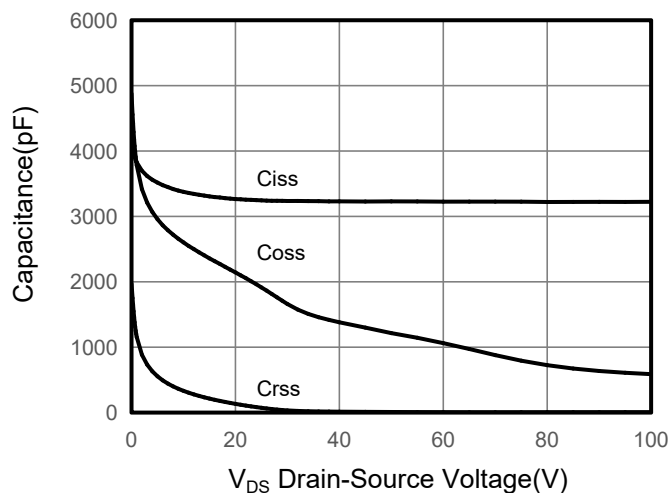
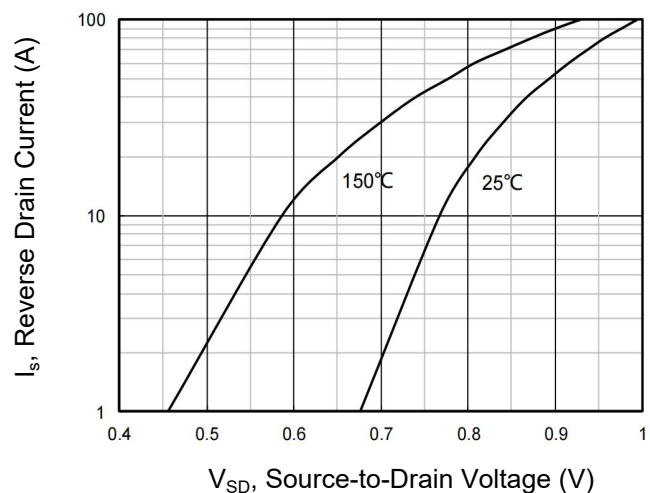


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

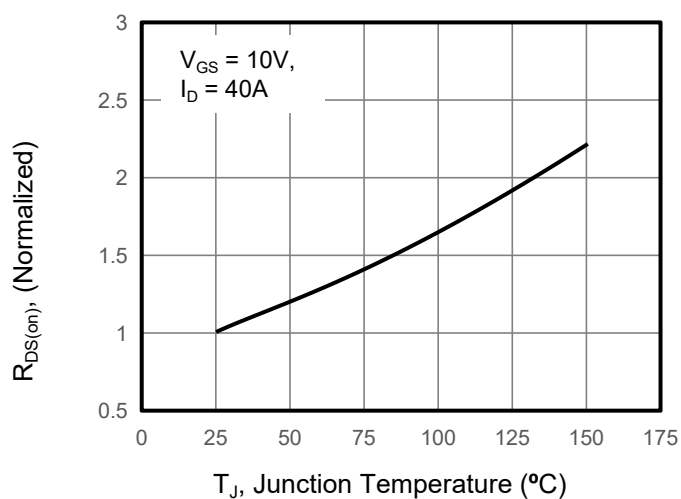


Figure 8. Safe Operation Area

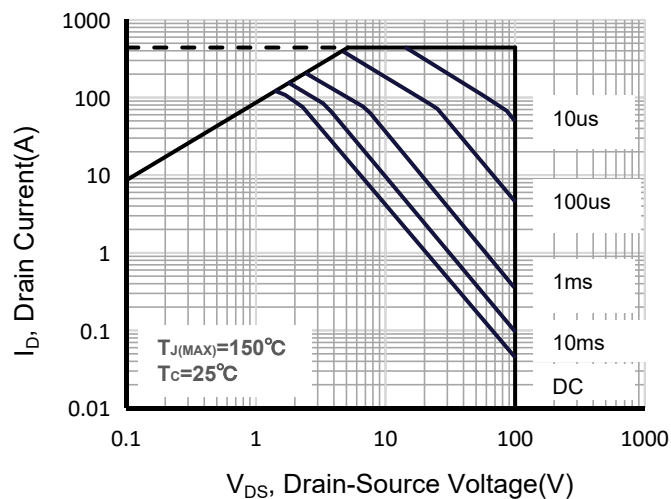


Figure 9. Maximum Continuous Drain Current vs Case Temperature

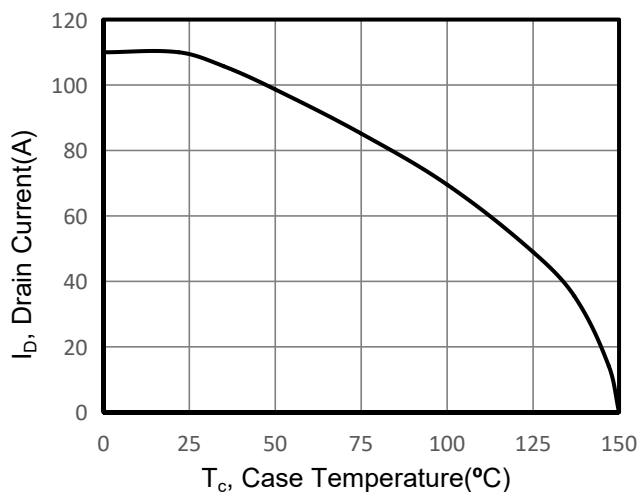
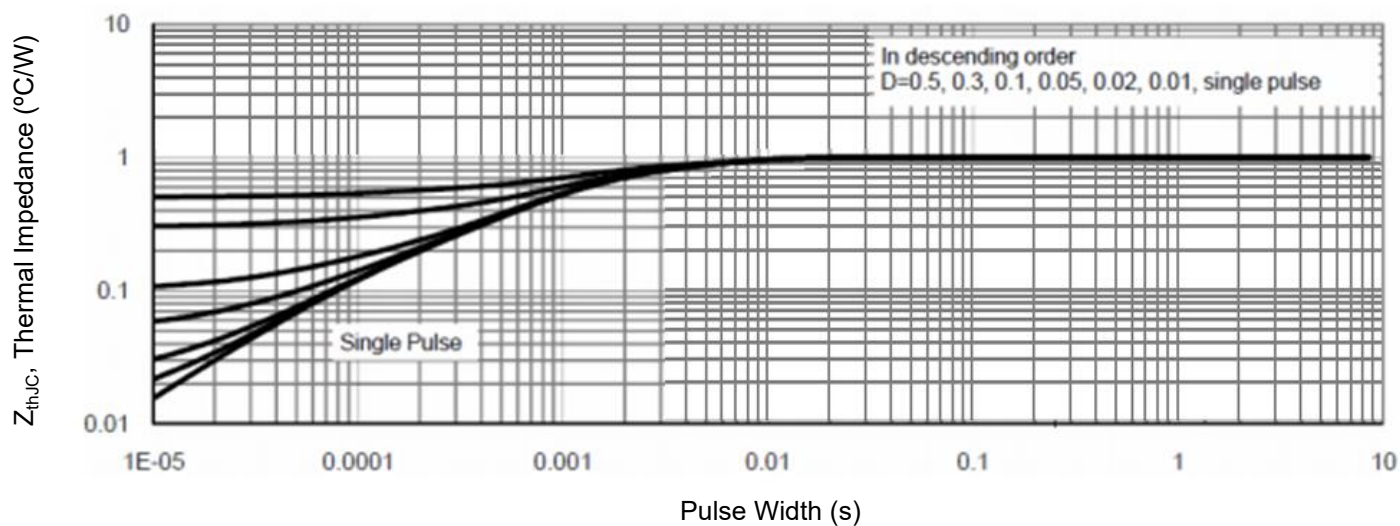
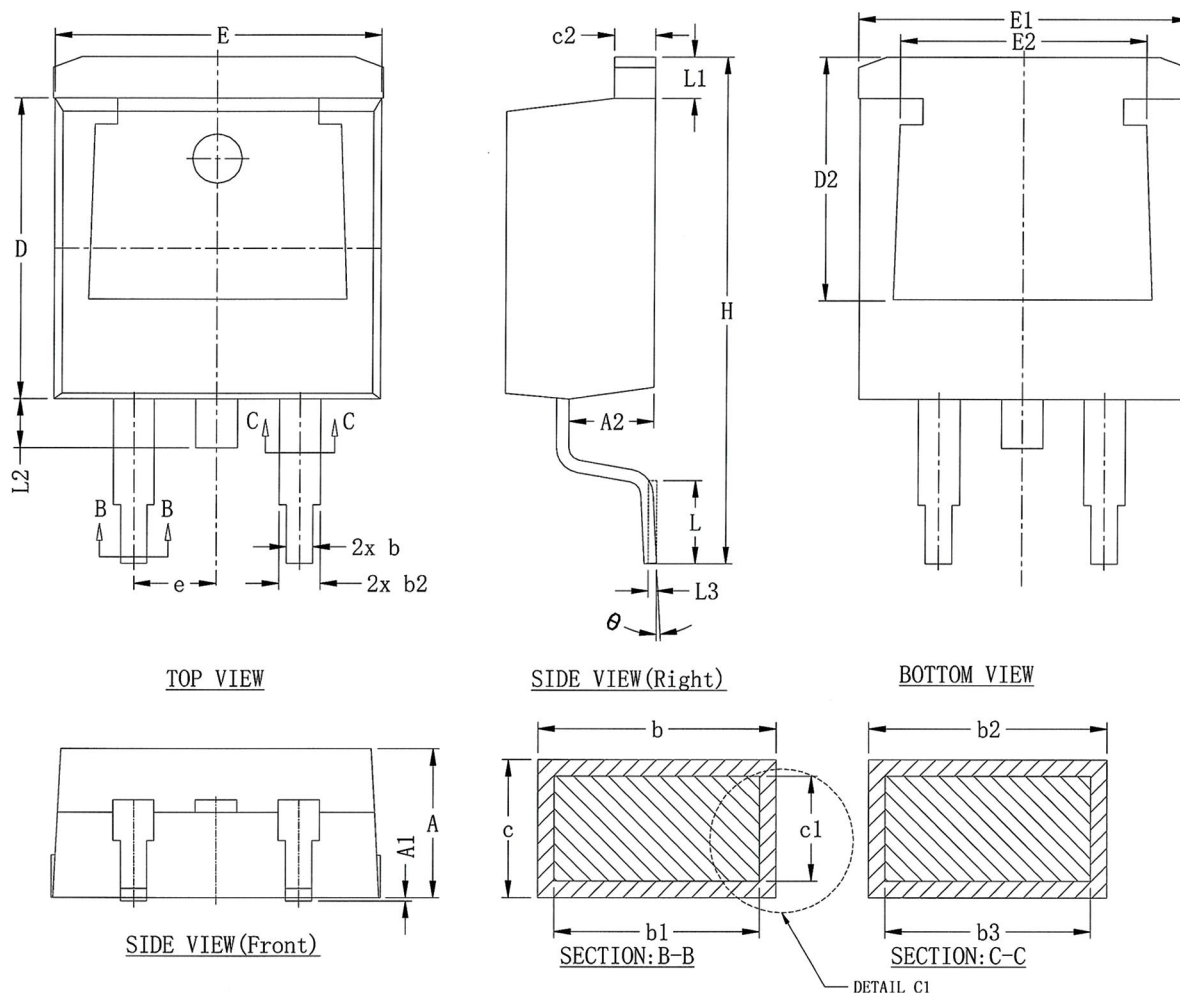


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-263 Package Information



DIM SYMBOL	MIN.	NOM.	MAX.	DIM SYMBOL	MIN.	NOM.	MAX.
A	4.450	4.550	4.650	D2	7.215	7.415	7.615
A1	0.000	—	0.150	E	9.900	10.000	10.100
A2	2.500	2.600	2.700	E1	9.900	10.100	10.300
b	0.753	0.853	0.953	E2	7.341	7.541	7.741
b1	0.713	0.813	0.913	e	2.540 BSC.		
b2	1.210	1.310	1.410	H	15.300	15.500	15.700
b3	1.170	1.270	1.370	L	2.340	2.540	2.740
c	0.330	0.421	0.521	L1	1.066	1.266	1.466
c1	0.281	0.381	0.481	L2	1.400	1.500	1.600
c2	1.210	1.310	1.410	L3	0.254 BSC.		
D	9.100	9.200	9.300	θ	0°	---	5°